

This listing of claims will replace all prior versions and listings of claims in the application.
Please add new claims 21-25 as follows.

Claims 1-15 were previously cancelled.

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16. (Previously amended) A semiconductor device having a gate oxide of multiple thickness for multiple transistors, the semiconductor device comprising:
 - a first gate oxide region having a first thickness for a first transistor, and
 - a second gate oxide region having a second thickness for a second transistor, the second gate oxide region being oxygen-implanted oxide, the second thickness being greater than the first thickness.
 17. (Original) The semiconductor device of claim 16 wherein the first thickness is less than about 30 Å.
 18. (Original) The semiconductor device of claim 16 wherein the first thickness is less than the second thickness by less than about 20 Å.
 19. (Original) The semiconductor device of claim 16 wherein the first gate oxide region is non-implanted oxide.
 20. (Original) The semiconductor device of claim 16, wherein the first gate oxide is oxygen implanted oxide, the implanted oxygen concentration being less than the implanted oxygen concentration of the second gate oxide region.
 21. (New) A semiconductor device having a gate oxide of multiple thickness for multiple transistors, the semiconductor device comprising:
 - a first gate oxide region having a first thickness for a first transistor, and
 - a second gate oxide region having a second thickness for a second transistor, the second gate oxide region including an oxygen-implanted oxide under a non-implanted oxide under a polysilicon gate, the second thickness being greater than the first thickness.
 22. (New) The semiconductor device of claim 21 wherein the first thickness is less than about 30 Å.
 23. (New) The semiconductor device of claim 21 wherein the first thickness is less than the second thickness by less than about 20 Å.

24. (New) The semiconductor device of claim 21 wherein the first gate oxide region is non-implanted oxide.

25. (New) The semiconductor device of claim 21, wherein the first gate oxide is oxygen implanted oxide, the implanted oxygen concentration being less than the implanted oxygen concentration of the second gate oxide region.
